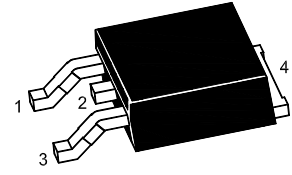


2SB772R

PNP SILICON EPITAXIAL POWER TRANSISTOR

These devices are intended for use in audio frequency power amplifier and low speed switching applications



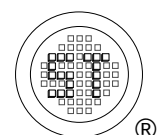
1. Base 2. Collector 3. Emitter 4. Collector
TO-252 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

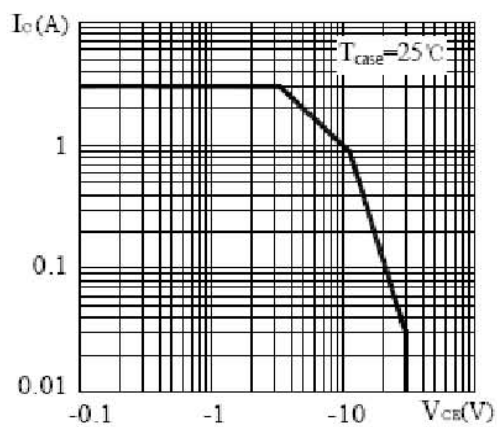
Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	40	V
Collector Emitter Voltage	$-V_{CEO}$	30	V
Emitter Base Voltage	$-V_{EBO}$	6	V
Collector Current	$-I_C$	3	A
Total Power Dissipation @ $T_a = 25^\circ\text{C}$	P_D	1.25	W
Total Power Dissipation @ $T_c = 25^\circ\text{C}$	P_D	10	W
Operating and Storage Junction Temperature Range	T_j, T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

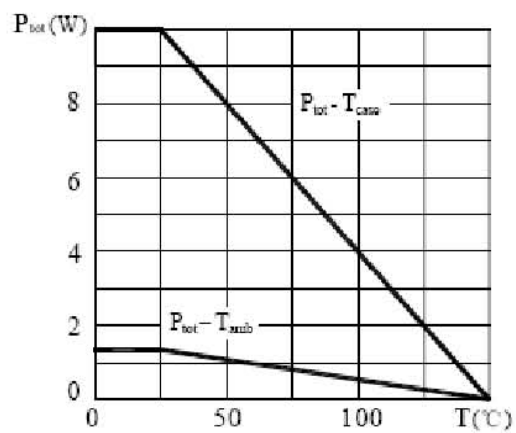
Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 2\text{ V}$, $-I_C = 1\text{ A}$	h_{FE} h_{FE}	100	200	-
Current Gain Group Q P		160	320	-
Collector Base Cutoff Current at $-V_{CB} = 30\text{ V}$	$-I_{CBO}$	-	1	μA
Collector Emitter Cutoff Current at $-V_{CE} = 30\text{ V}$	$-I_{CEO}$	-	1	μA
Emitter Base Cutoff Current at $-V_{EB} = 3\text{ V}$	$-I_{EBO}$	-	1	μA
Collector Base Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	40	-	V
Collector Emitter Breakdown Voltage at $-I_C = 5\text{ mA}$	$-V_{(BR)CEO}$	30	-	V
Emitter Base Breakdown Voltage at $-I_E = 100\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	6	-	V
Collector Emitter Saturation Voltage at $-I_C = 2\text{ A}$, $-I_B = 200\text{ mA}$	$-V_{CE(sat)}$	-	0.5	V
Base Emitter Saturation Voltage at $-I_C = 2\text{ A}$, $-I_B = 200\text{ mA}$	$-V_{BE(sat)}$	-	2	V
Current Gain Bandwidth Product at $-V_{CE} = 5\text{ V}$, $-I_C = 100\text{ mA}$,	f_T	50	-	MHz



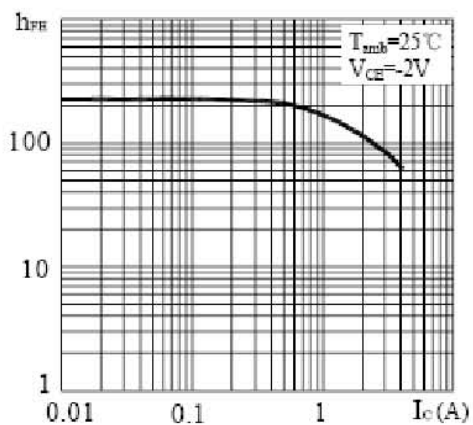
SOA (DC)



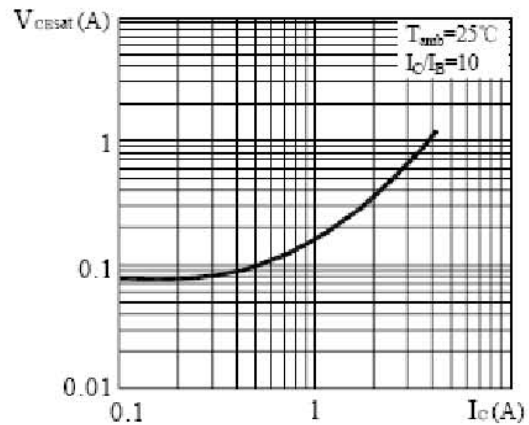
P_C -T



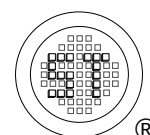
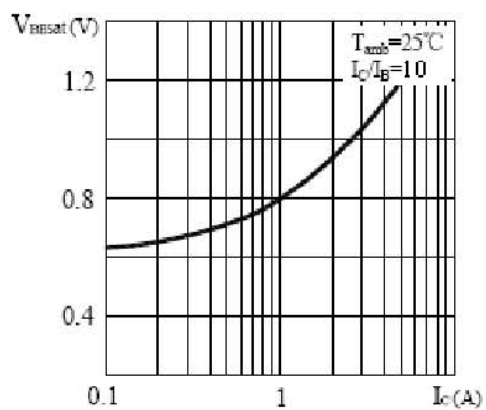
h_{FE} - I_C



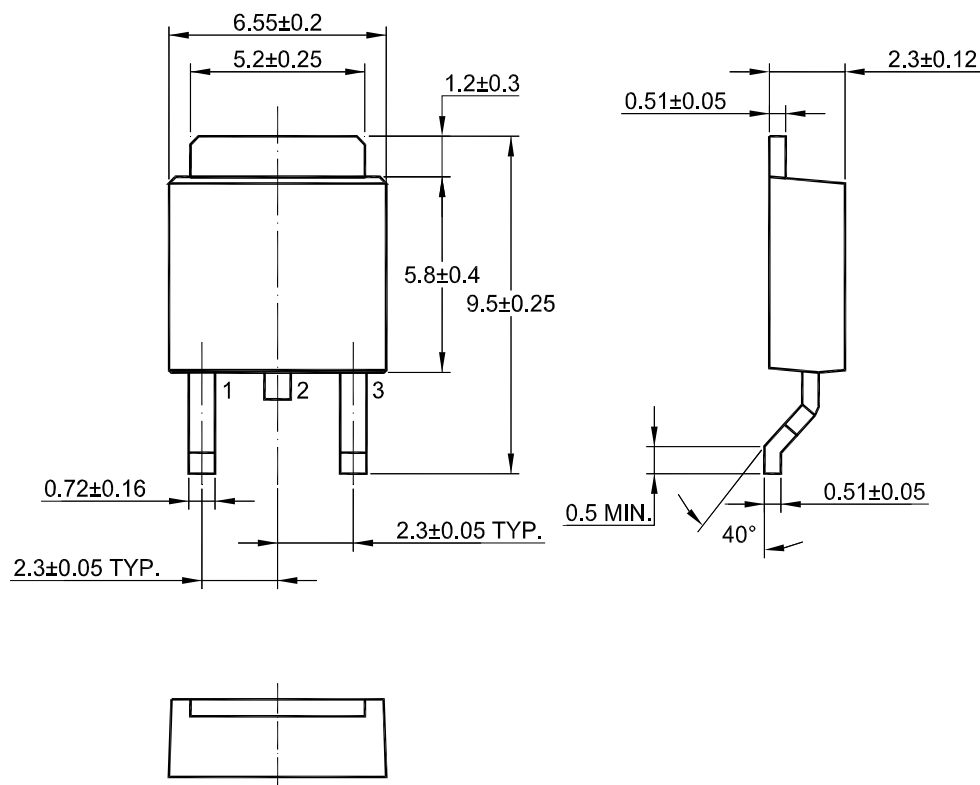
$V_{CE(sat)}$ - I_C



$V_{BE(sat)}$ - I_C



TO-252 PACKAGE OUTLINE



Dimensions in mm

